

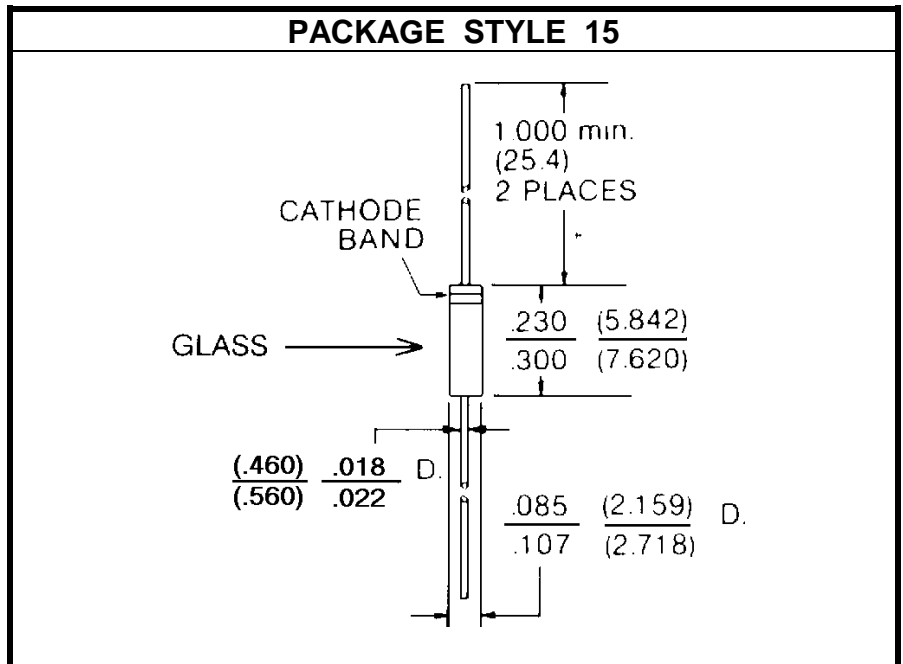
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6019M** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law ($n = 0.5$).

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	70 V
P_{DISS}	250 mW @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS	
V_B	I _R = 10 μA	70			V	
C_T	V _R = 4.0 V	f = 1.0 MHz	31.35	33.0	34.65	pF
ΔC_T	C _T = 0 V / C _T = 60 V	f = 1.0 MHz	7.4			RATIO
ΔC_T	C _T = 8.0 V / C _T = 60 V	f = 1.0 MHz	2.50		2.60	RATIO
Q	V _R = 4.0 V	f = 50 MHz	800			
T_C	V _R = 4.0 V			300	Ppm/°C	